

**Description**

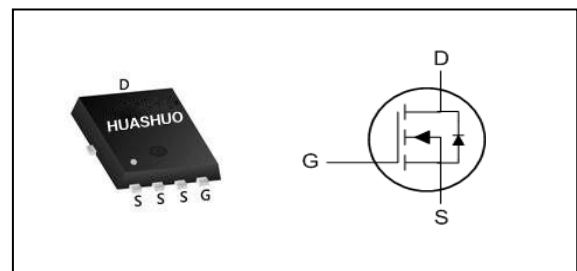
- Advanced Trench MOS Technology
- Low Gate Charge
- Low  $R_{DS(ON)}$
- 100% EAS Guaranteed
- Green Device Available

**Product Summary**

$V_{DS}$	60	V
$R_{DS(ON),typ}$	4.4	m $\Omega$
$I_D$	60	A

**Application**

- Motor Control.
- DC/DC Converter.
- Synchronous rectifier applications.

**PRPAK3X3 Pin Configuration**

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current <sup>1</sup>	60	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current <sup>1</sup>	37	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	130	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	93	mJ
$I_{AS}$	Avalanche Current	43	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation <sup>4</sup>	45	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	55	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	2.8	$^\circ\text{C/W}$

**N-Ch 60V Fast Switching MOSFETs**
**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
B <sub>V</sub> DSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	60	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	---	4.4	5.2	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	---	6.4	7.8	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.65	2.3	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =48V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.3	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =20A	---	33	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	18	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	6	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =20A	---	7.5	---	ns
T <sub>r</sub>	Rise Time		---	6	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	29	---	
T <sub>f</sub>	Fall Time		---	7.5	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, f=1MHz	---	1670	---	pF
C <sub>oss</sub>	Output Capacitance		---	438	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	25	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	60	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>		---	---	130	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =15A, di/dt=100A/μs, T <sub>J</sub> =25°C	---	23	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	60	---	nC

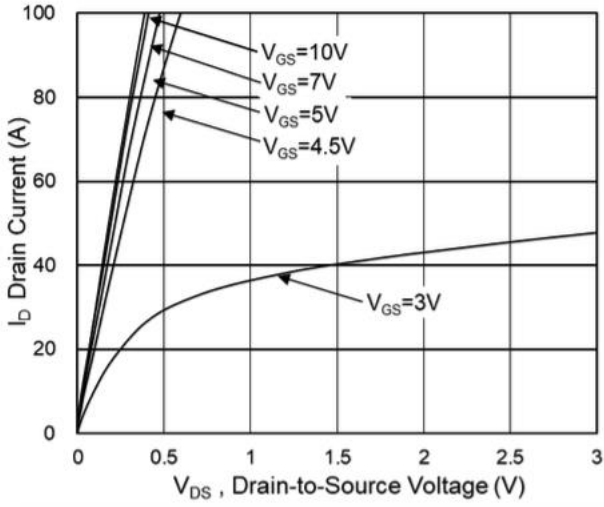
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=43A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

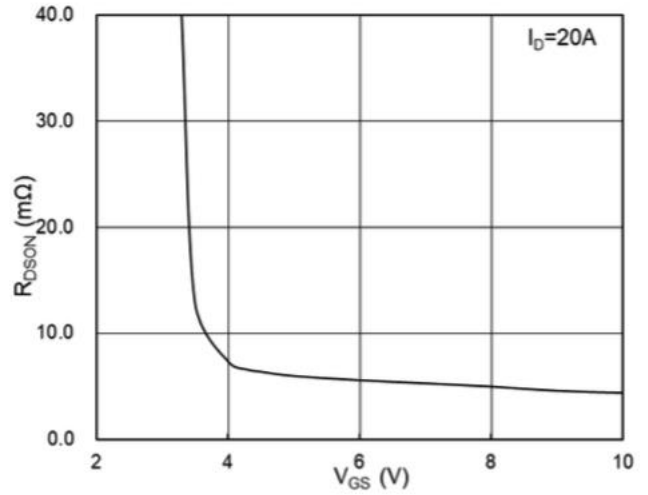


**N-Ch 60V Fast Switching MOSFETs**

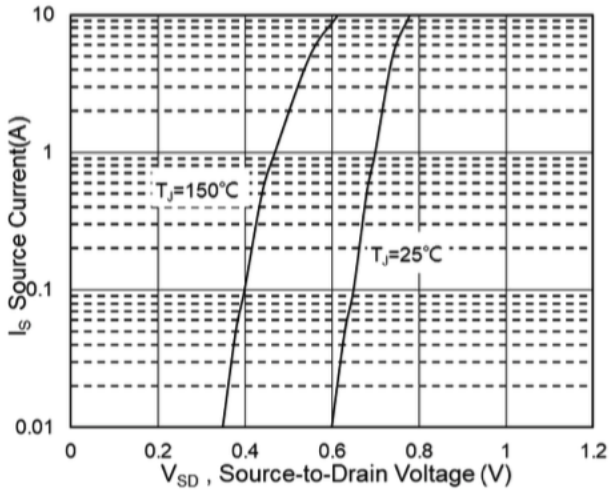
**Typical Characteristics**



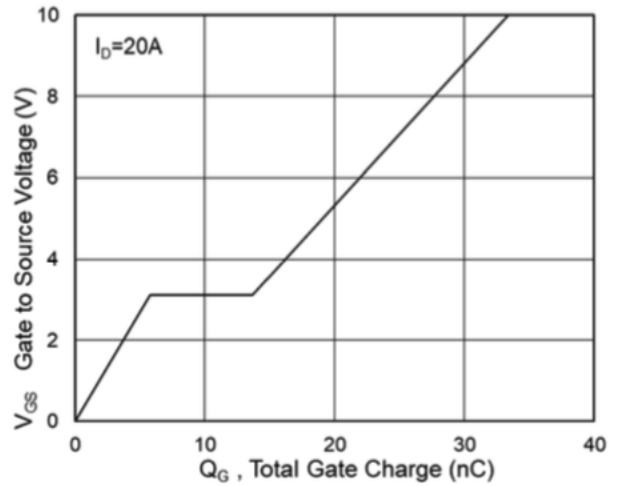
**Fig.1 Typical Output Characteristics**



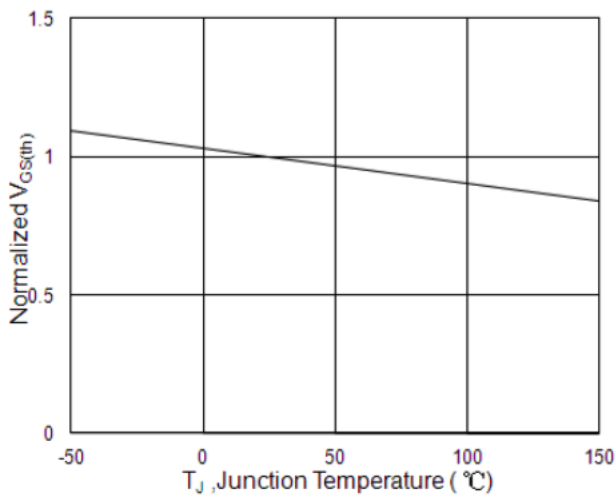
**Fig.2 On-Resistance vs. Gate-Source**



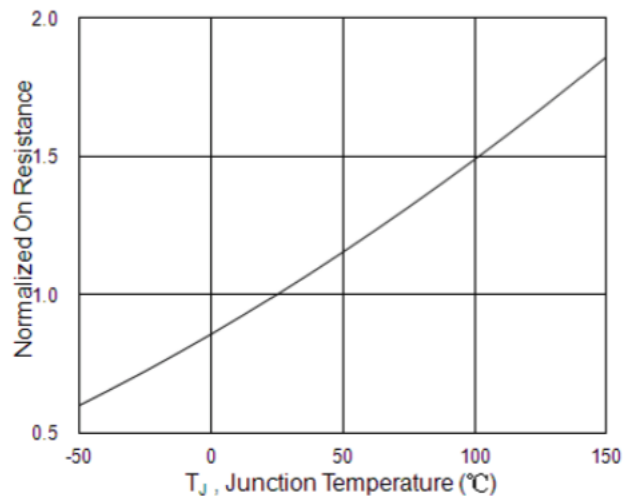
**Fig.3 Source Drain Forward Characteristics**



**Fig.4 Gate-Charge Characteristics**



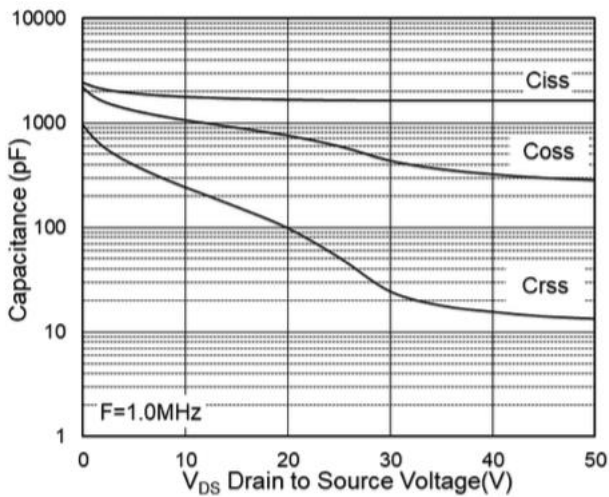
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



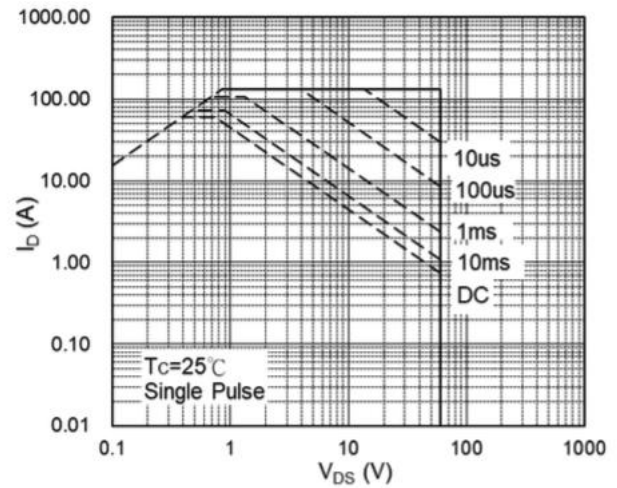
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



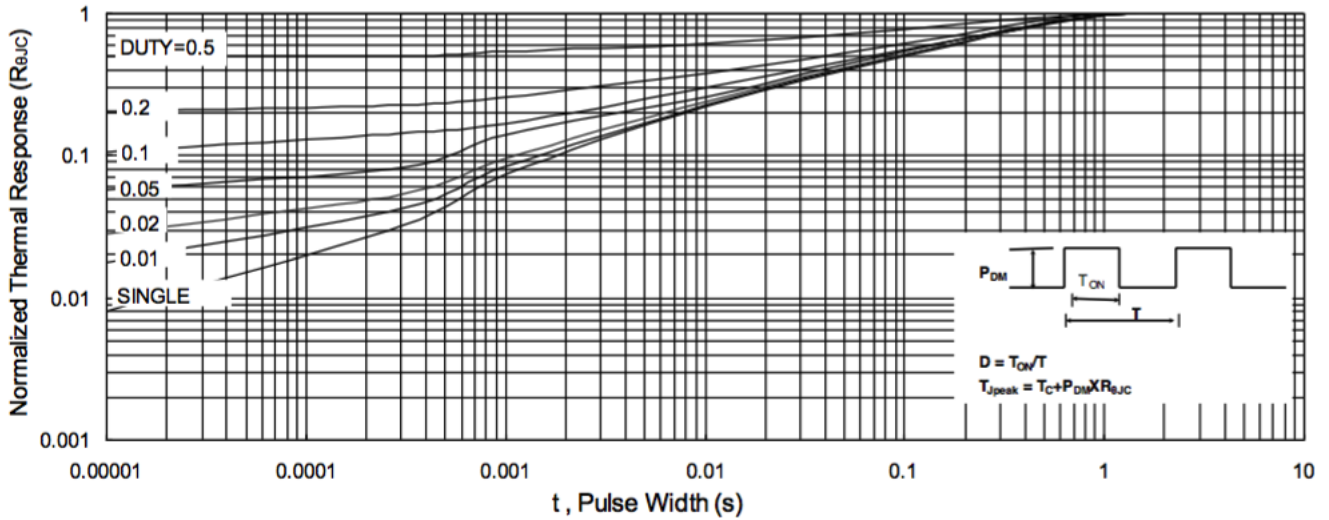
**N-Ch 60V Fast Switching MOSFETs**



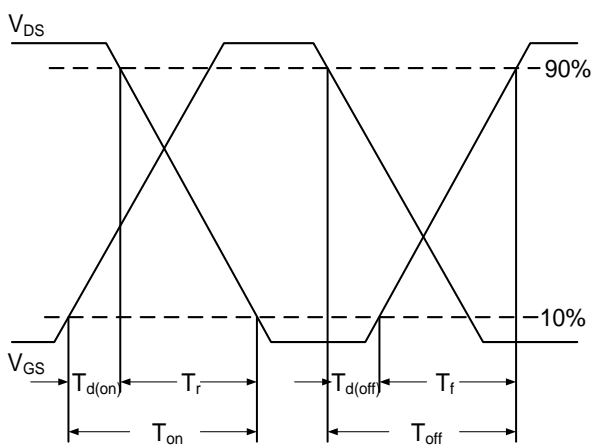
**Fig.7 Capacitance**



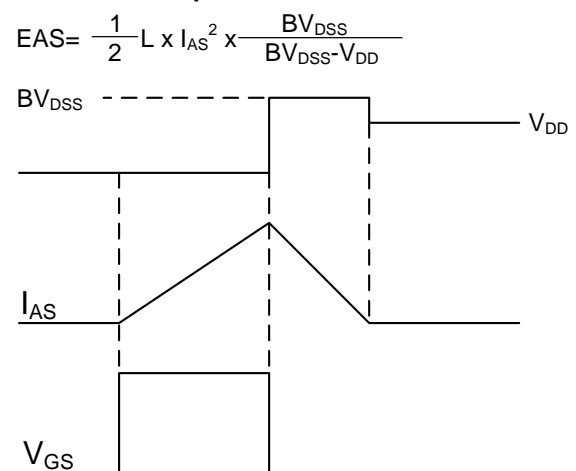
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**

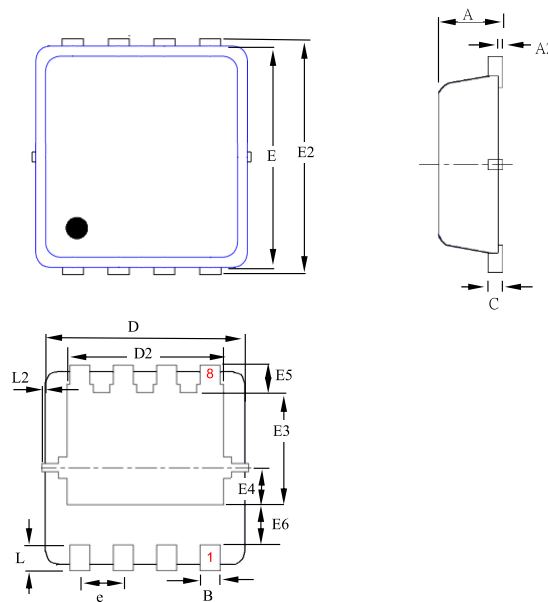


**Fig.11 Unclamped Inductive Switching Waveform**

## Ordering Information

Part Number	Package code	Packaging
HSBB6066	PRPAK3*3	3000/Tape&Reel

**PRPAK 3\*3(E) Single Outline**



SYMBOLS	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.028	0.031	0.035
A2	0.00	--	0.05	0.000	--	0.002
B	0.24	0.30	0.35	0.009	0.012	0.014
C	0.10	0.15	0.25	0.004	0.006	0.010
D	2.90	3.00	3.20	0.114	0.118	0.126
D2	2.15	2.35	2.59	0.085	0.093	0.102
E	2.90	3.00	3.12	0.114	0.118	0.123
E2	3.05	3.20	3.45	0.120	0.126	0.136
E3	1.55	1.75	1.95	0.061	0.069	0.077
E4	0.48	0.58	0.68	0.019	0.023	0.027
E5	0.28	0.43	0.58	0.011	0.017	0.023
E6	0.43	0.63	0.87	0.017	0.025	0.034
L	0.30	0.40	0.50	0.012	0.016	0.020
L2	0.00	--	0.10	0.000	--	0.004
e	--	0.65	--	--	0.026	--